

CODE I1

NOTES:

1. All dimensions are in millimeter;
2. Tolerance is $\pm 0.25\text{mm}$, unless other specified;
3. Pin length, housing color, marking no. & circuit diagram can be customized;
4. Specifications are subject to change without notice.


Chip Material: InGaN Blue LED Chip
ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

PARAMETER	SYMBOL	MAXIMUM RATING	UNIT
Power Dissipation	PD	96	mW
Peak Forward Current (1/10 Duty Cycle, 0.1 Ms Pulse Width)	IPEAK	100	mA
DC Forward Current	IF	30	mA
Reverse Voltage	VR	5	V
Operating Temperature Range	TA	-40°C to +85°C	
Storage Temperature Range	TSTG	-40°C to +85°C	
Solder temperature 1/16 inch below seating plane for 3 seconds at 260°C			

ELECTRICAL OPTICAL CHARACTER AND CURVES (Ta = 25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	LOCATION	TEST CONDITION
Forward Voltage	VF	-	3.00	3.40	V	Per Segment	IF = 20mA
Luminous Intensity	Iv	80	90	100	mcd	Per Segment	IF = 20mA
Peak Emission Wavelength	λp	-	472	-	nm	Per Segment	IF = 20mA
Dominant Emission Wavelength	λd	465	470	475	nm	Per Segment	IF = 20mA
Spectral Line Half-Width	Δλ1/2	-	25	-	nm	Per Segment	IF = 20mA
Capacitance	C	-	100	-	pF	Per Segment	VF=0V;f=1MHz
Reverse Current	IR	-	-	10	uA	Per Segment	VR = 5V

Note:

- Luminous intensity tolerance is ±10%;**
- Dominant Emission Wavelength tolerance is ±5%.**

■ **Typical Electro-Optical Characteristic Curve:**

FIG. 1 Forward Current Vs. Forward Voltage

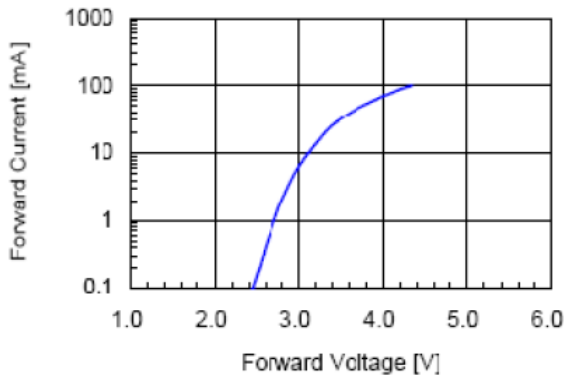


FIG. 2 Relative Intensity Vs. Forward Current

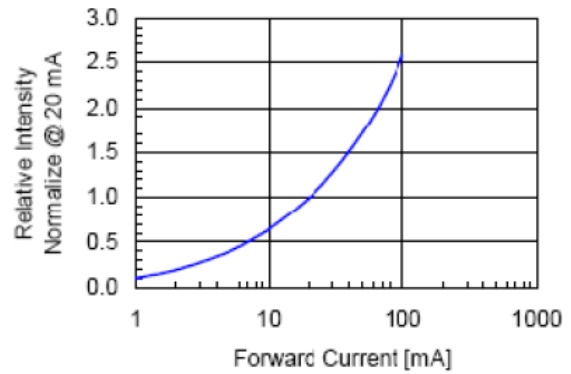


FIG. 3 Forward Voltage Vs. Temperature

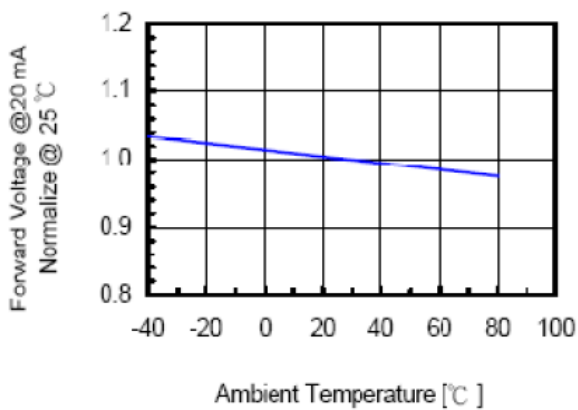


FIG. 4 Relative Intensity Vs. Temperature

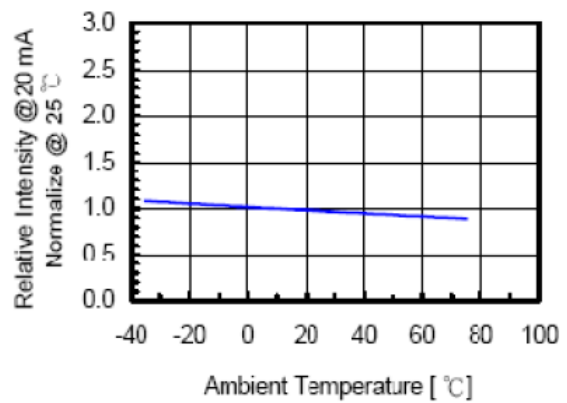


FIG. 5 Relative Intensity Vs. Wavelength

